

CMPD914

**SURFACE MOUNT
HIGH SPEED
SILICON SWITCHING DIODE**



www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD914 is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, designed for high speed switching applications.

MARKING CODE: C5D



SOT-23 CASE

MAXIMUM RATINGS: (T_A=25°C)

Continuous Reverse Voltage	V _R	75	V
Peak Repetitive Reverse Voltage	V _{RRM}	100	V
Continuous Forward Current	I _F	250	mA
Peak Repetitive Forward Current	I _{FRM}	250	mA
Peak Forward Surge Current, tp=1.0μs	I _{FSM}	4.0	A
Peak Forward Surge Current, tp=1.0ms	I _{FSM}	2.0	A
Peak Forward Surge Current, tp=1.0s	I _{FSM}	1.0	A
Power Dissipation	P _D	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

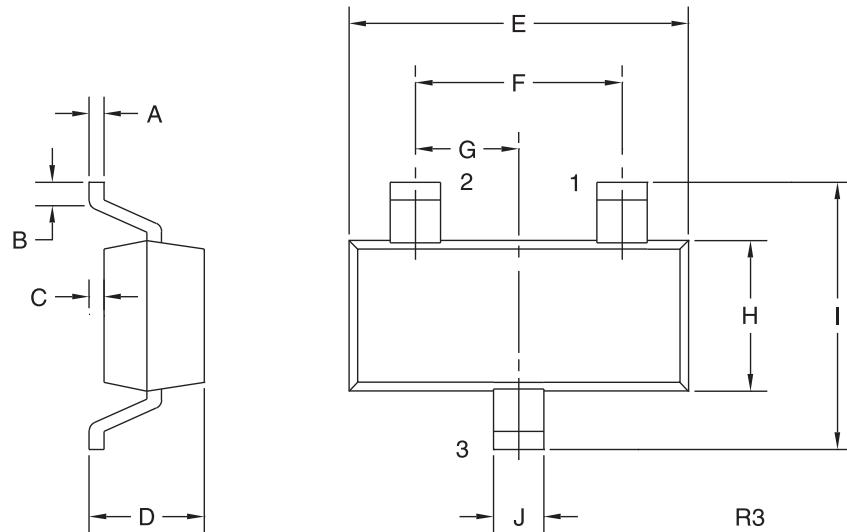
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =20V		25	nA
I _R	V _R =75V		5.0	μA
BV _R	I _R =100μA	100		V
V _F	I _F =10mA		1.0	V
C _T	V _R =0, f=1.0MHz		4.0	pF
t _{rr}	I _R =I _F =10mA, R _L =100Ω, Rec. to 1.0mA		4.0	ns

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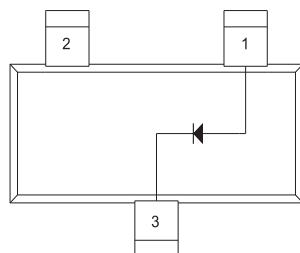
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Central
Semiconductor Corp.™

SOT-23 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Anode
- 2) No Connection
- 3) Cathode

MARKING CODE: C5D

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R6 (25-January 2010)